



GP2M005A050HG Information



For Reference Only

Part Number GP2M005A050HG

ManufacturerGlobal Power Technologies GroupCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 4.5A TO220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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GP2M005A050HG Specifications

Manufacturer Part Number GP2M005A050HG Manufacturer Global Power Technologies Group Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 4.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 98.4W (Tc) Rds On (Max) @ Id, Vgs 1.5 Ohm @ 2.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Torin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ### 30V ### 30V ### 50 (Max) ### 30V ### 50 (Max) ### 30V ### 64 (Pr eather ### 25V ### 25V ### 30V ###	Manufacturer Part Number	GP2M005A050HG
Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 4.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 98.4W (Tc) Rds On (Max) @ Id, Vgs 1.5 Ohm @ 2.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Manufacturer	Global Power Technologies Group
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Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 4.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 98.4W (Tc) Rds On (Max) @ Id, Vgs 1.5 Ohm @ 2.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C4.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds645pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)98.4W (Tc)Rds On (Max) @ Id, Vgs1.5 Ohm @ 2.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C4.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds645pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)98.4W (Tc)Rds On (Max) @ Id, Vgs1.5 Ohm @ 2.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Series	-
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C4.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds645pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)98.4W (Tc)Rds On (Max) @ Id, Vgs1.5 Ohm @ 2.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sty @ 250μA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4.5A (Tc) 5v @ 250μA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4.5PF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.5 Ohm @ 2.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds645pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)98.4W (Tc)Rds On (Max) @ Id, Vgs1.5 Ohm @ 2.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 98.4W (Tc) Rds On (Max) @ Id, Vgs 1.5 Ohm @ 2.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	4.5A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.5 Ohm @ 2.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.5 Ohm @ 2.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)98.4W (Tc)Rds On (Max) @ Id, Vgs1.5 Ohm @ 2.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	15nC @ 10V
FET Feature - Power Dissipation (Max) 98.4W (Tc) Rds On (Max) @ Id, Vgs 1.5 Ohm @ 2.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	645pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.5 Ohm @ 2.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs1.5 Ohm @ 2.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Power Dissipation (Max)	98.4W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	1.5 Ohm @ 2.25A, 10V
Supplier Device Package TO-220 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220
Report errors?	Package / Case	TO-220-3
100 post 511010 r		Report errors?

GP2M005A050HG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

GP2M005A050HG Payment Methods





















GP2M005A050HG Shipping Methods













If you have any question about GP2M005A050HG, please do not hesitate to contact us!

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